

| | Hits | Search Text | DBs |
|----|------|---|---|
| 1 | 600 | thin adj film with (pattern\$3 etch\$3) with (ion adj beam) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 2 | 617 | thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 3 | 17 | ((thin adj film near2 (pattern\$3 etch\$3) near2 ((ion cluster focused) near beam)) with (strip strippable ash\$3 photoresist mask) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 4 | 19 | ((thin adj film near2 (pattern\$3 etch\$3) near2 ((ion cluster focused) near beam)) same (strip strippable ash\$3 photoresist mask) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 5 | 75 | thin adj film near2 (pattern\$3 etch\$3) near2 ((ion cluster focused) near beam) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 6 | 185 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) same (strip strippable ash\$3 photoresist mask) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 7 | 151 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) with (strip strippable ash\$3 photoresist mask) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 8 | 2 | ((thin adj film near2 (pattern\$3 etch\$3) near2 ((ion cluster focused) near beam)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 9 | 23 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) same (strip strippable ash\$3 photoresist mask)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 10 | 26 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 11 | 3 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask)) not (((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) same (strip strippable ash\$3 photoresist mask)) and (ION IONIC CLUSTER CHARGED PARTICLE) NEAR BEAM near (etch\$3 pattern\$3) near (strippable photoresist resist mask)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 12 | 15 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and ((etch\$3 pattern\$3) near (resist photoresist) near ((ION IONIC CLUSTER focused CHARGED PARTICLE) NEAR BEAM)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 13 | 58 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and lift adj off | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 14 | 27 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and lift adj off) and magnet\$5 | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 15 | 24 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and lift adj off) and magnet\$2 with thin adj film | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 16 | 5 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam)) and lift adj off) and magnet\$2 near thin adj film | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 17 | 69 | thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) and (liftoff lift-off lift adj off) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 18 | 16 | thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) same (liftoff lift-off lift adj off) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |

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|----|------|--|---|
| 19 | 53 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) and (liftoff lift-off lift adj off)) not (thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) same (liftoff lift-off lift adj off))) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 20 | 3241 | focused adj ion adj beam | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 21 | 0 | ((thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) and (liftoff lift-off lift adj off)) not (thin adj film with (pattern\$3 etch\$3) with ((ion cluster focused) near beam) same (liftoff lift-off lift adj off))) and (focused adj ion adj beam with pattern\$3 with (mask resist photoresist)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 22 | 180 | focused adj ion adj beam with pattern\$3 with (mask resist photoresist) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 23 | 2 | focused adj ion adj beam adj lithography with pattern\$3 with (mask resist photoresist) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 24 | 42 | focused adj ion adj beam adj lithography | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 25 | 9 | (US-4405710-\$ or US-5236547-\$ or US-5399546-\$ or US-5446016-\$ or US-5506197-\$ or US-5793579-\$ or US-6245249-\$ or US-6391216-\$ or US-6407547-\$).did. | USPAT |
| 26 | 4306 | etch\$3 same ground\$3 with (film layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 27 | 361 | etch\$3 with ground\$3 near (film layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 28 | 51 | etch\$3 near ground\$3 near (film layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 29 | 44 | etch\$3 adj ground\$3 near (film layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 30 | 36 | etch\$3 adj ground\$3 adj (film layer) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 31 | 2 | (etch\$3 adj ground\$3 adj (film layer)) and (ion adj beam FIB RIBe) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 32 | 2 | (etch\$3 adj ground\$3 near (film layer)) and (ion adj beam FIB RIBe) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 33 | 20 | (etch\$3 with ground\$3 near (film layer)) and (ion adj beam FIB RIBe) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 34 | 172 | (etch\$3 same ground\$3 with (film layer)) and (ion adj beam FIB RIBe) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 35 | 3 | (etch\$3 near ground\$3 near (film layer)) and (ion adj beam FIB RIBe) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 36 | 17 | ((etch\$3 with ground\$3 near (film layer)) and (ion adj beam FIB RIBe)) not ((etch\$3 near ground\$3 near (film layer)) and (ion adj beam FIB RIBe)) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |
| 37 | 22 | (etch\$3 same ground\$3 with (film layer)) and (focused adj ion adj beam FIB) | USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB |